

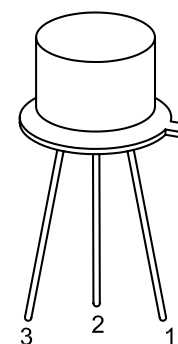
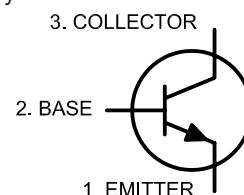


Description:

This is a Silicon NPN transistor in a TO-39 type case designed primarily for amplifier and switching applications. This device features high breakdown voltage, low leakage current, low capacity, and beta useful over an extremely wide current range.

**RoHS
Compliant**

NPN



Absolute Maximum Ratings:

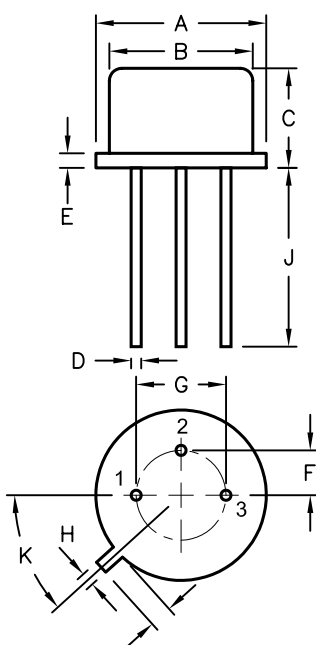
Characteristic	Symbol	Rating
Collector-Base Voltage	V_{CB0}	60V
Collector-Emitter Voltage	V_{CE0}	40V
Emitter - Base Voltage	V_{EB0}	5V
Continuous Collector Current	I_C	0.7A
Total Device Dissipation ($T_c = +25^\circ\text{C}$) Derate above 25°C	P_D	800mW 4.6mW/ $^\circ\text{C}$
Total Device Dissipation ($T_c = +25^\circ\text{C}$) Derate above 25°C	P_D	5W 28.6mW/ $^\circ\text{C}$
Operating Junction Temperature Range	T_J	-65°C to $+200^\circ\text{C}$
Storage Temperature Range	T_{STG}	-65°C to $+200^\circ\text{C}$
Thermal Resistance, Junction-to-Case	R_{thJC}	35°C/W
Lead Temperature (During Soldering, 1/16" from case, 60sec max.)	T_L	300°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ Unless otherwise specified)

Parameter	Symbol	Test Conditions	Min.	Max.	Unit.
OFF Characteristics					
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 0.1\text{mA}, I_B = 0$	40	-	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}, I_E = 0$	60	-	
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}, I_C = 0$	5	-	
Emitter Cut-Off Current	I_{EBO}	$V_{BE} = 4\text{V}, I_C = 0$	-	0.01	μA
On Characteristics (Note 1)					
DC Current Gain	h_{FE}	$V_{CE} = 10\text{V}, I_C = 150\text{mA}$	50	-	-
		$V_{CE} = 2.5\text{V}, I_C = 150\text{mA}$	40	-	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 150\text{mA}, I_B = 15\text{mA}$	-	1.4	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 150\text{mA}, I_B = 15\text{mA}$	-	1.7	V

Parameter	Symbol	Test Conditions	Min.	Max.	Unit.
Small-Signal Characteristics					
Current Gain-Bandwidth Product	f_T	$V_{CE} = 10V, I_C = 50mA, f = 20MHz$	100	400	MHz
Output Capacitance	C_{obo}	$V_{CB} = 10V, I_E = 0, f = 1MHz$	-	12	pF
Input Capacitance	C_{ibo}	$V_{BE} = 500mV, I_C = 0, f = 1MHz$	-	60	pF

Note 1. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 1\%$



1. EMITTER
2. BASE
3. COLLECTOR

Dimensions	A	B	C	D	E	F	G	H	I	J	K
Min.	8.5	7.74	6.09	0.4	-	2.41	4.82	0.71	0.73	12.7	42°
Max.	9.39	8.50	6.6	0.53	0.88	2.66	5.33	0.86	1.02	-	48°

Dimensions : Millimetres

Part Number Table

Description	Part Number
Bipolar Transistor, NPN, 700mA, 40V, TO-39	2N3053

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